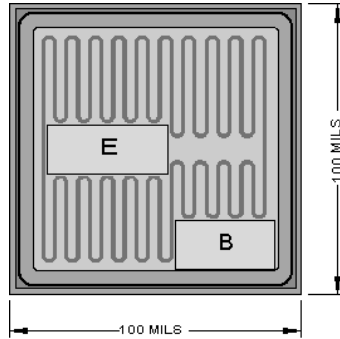


**Chip Type 2C5004**  
**Geometry 9202**  
**Polarity NPN**

**Generic Packaged Parts:**  
**2N5002, 2N5004**



[Request Quotation](#)

Chip type **2C5004** by Semicoa Semiconductors provides performance similar to these devices.

**Part Numbers:**  
[2N5002](#), [2N5004](#)

**Product Summary:**

**APPLICATIONS:** Designed for medium power amplifier and switching and wide band amplifier applications.

**Features:**

- Medium power ratings

Mechanical Specifications		
Metallization	Top	Al - 37.5 kÅ min.
	Backside	Au - 6.5 kÅ nom.
Bonding Pad Size	Emitter	12 mils x 40 mils
	Base	12 mils x 30 mils
Die Thickness	8 mils nominal	
Chip Area	100 mils x 100 mils	
Top Surface	Silox Passivated	

Electrical Characteristics				
$T_A = 25^\circ\text{C}$				
Parameter	Test conditions	Min	Max	Unit
$BV_{CEO}$	$I_C = 10 \text{ mA}, I_E = 0$	80	---	V dc
$I_{CEO}$	$V_{CE} = 40 \text{ V}, I_B = 0$	---	50	$\mu\text{A}$
$I_{CES}$	$V_{CE} = 100 \text{ V}, V_{BE} = 0$	---	1.0	mA
$I_{EBO}$	$V_{EB} = 5.5 \text{ V}, I_C = 0$	---	1.0	mA
$\eta_{FE}$	$I_C = 50 \text{ mA dc}, V_{CE} = 5.0 \text{ V}$	50	---	---

*Due to limitations of probe testing, only dc parameters are tested. This must be done with pulse width less than 300  $\mu\text{s}$ , duty cycle less than 2%.*